

Segmented Rectifying and Blocking Contacts on Germanium Planar Detectors

Principal Investigator: Ethan Hull, Ph.D.

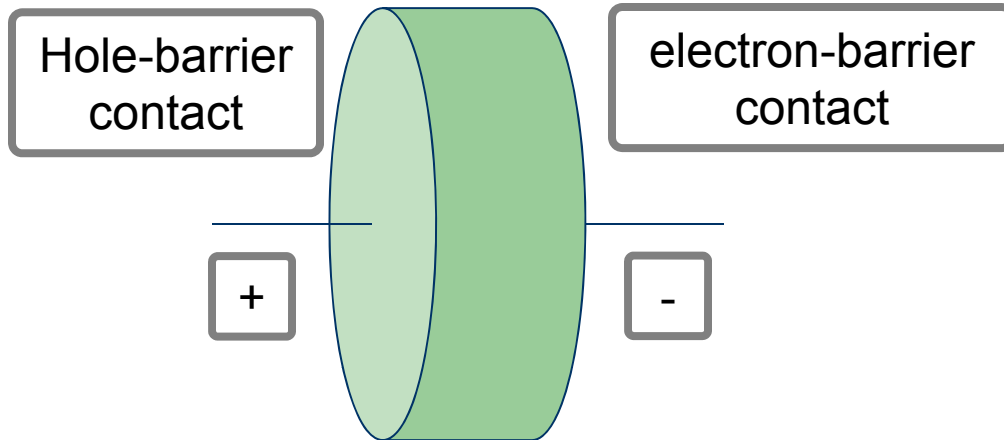
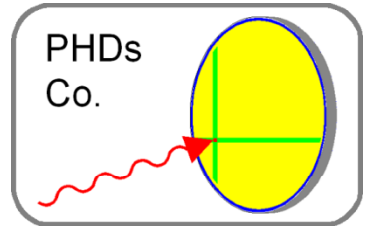
DE-SC0002477

Phase II: 8/15/2010-8/14/2012

New detector contact technologies have been developed for the fabrication of segmented planar germanium detectors. Yttrium metal contacts have the correct combination of physical properties to provide segmented low-noise detector contacts. Photolithographic yttrium segmentation techniques are being developed to provide relatively fine and well-defined contact features.

1. Rectifying and Blocking germanium detector contacts
2. Phase II Program Goals
3. Progress During Phase II

Rectifying and Blocking germanium detector contacts



E Field – depletion and charge collection
~ 500 – 5000 V/cm

Low leakage current (~ 10 pA) – low noise

Good electrical connection to Ge – low noise

HPGe

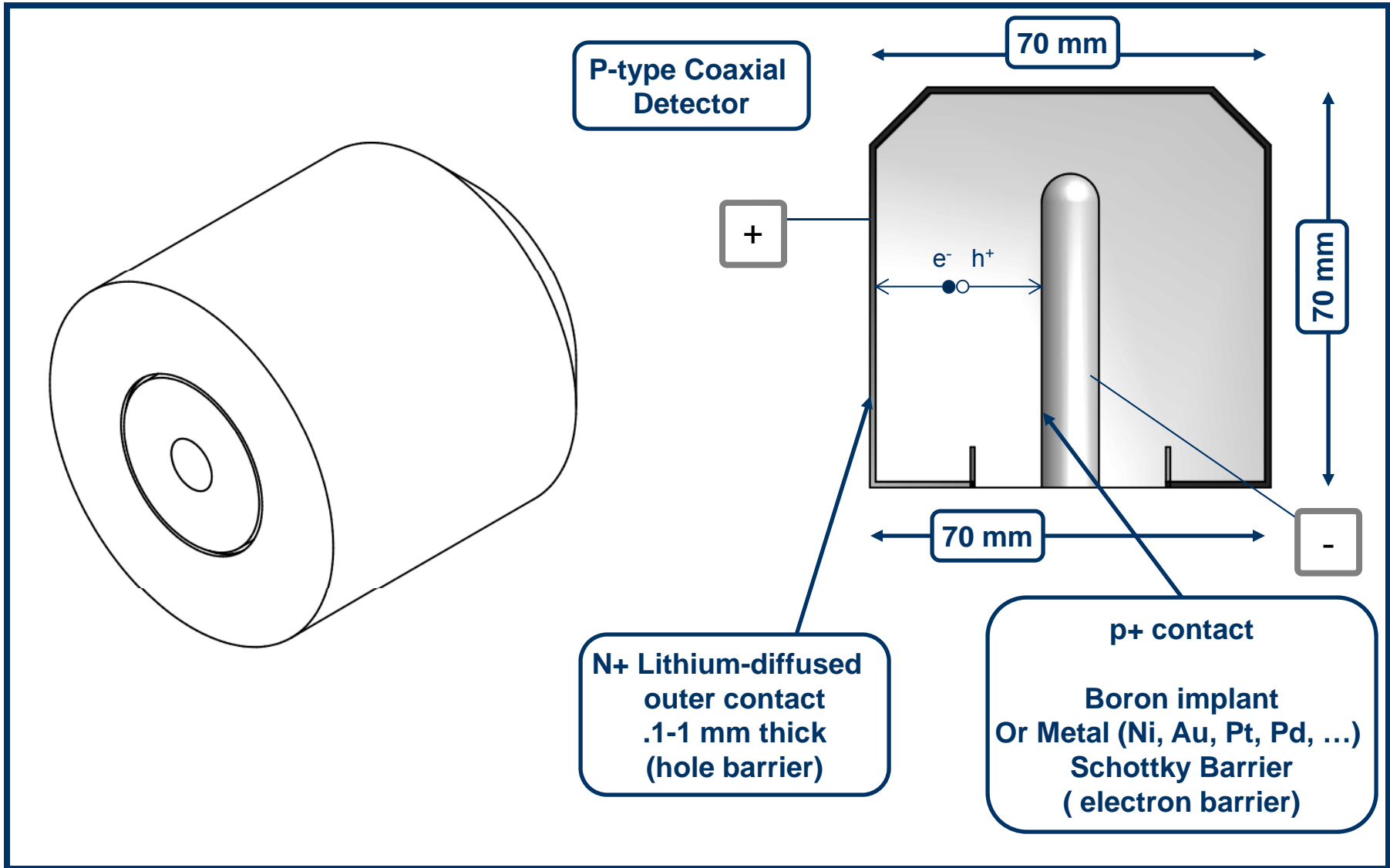
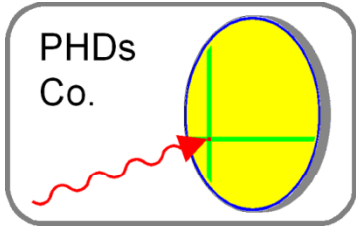
$$|N_A - N_D| \sim 10^{10} / \text{cm}^3$$
$$\mu \sim 4 \times 10^4 \text{ cm}^2/\text{Vs} (77 \text{ K})$$

$$\rho \sim 15 \text{ k}\Omega \text{ cm}$$
$$1 \text{ cm}^3, 1 \text{ V} \sim 67 \mu\text{A} \text{ !!!!}$$

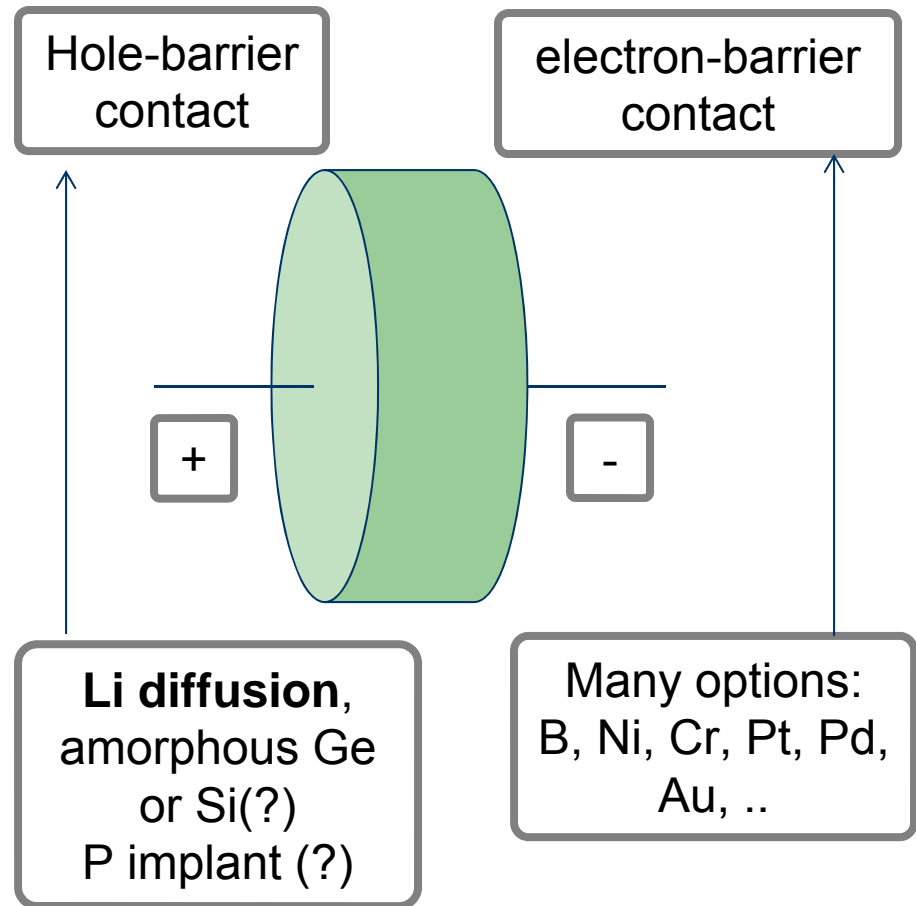
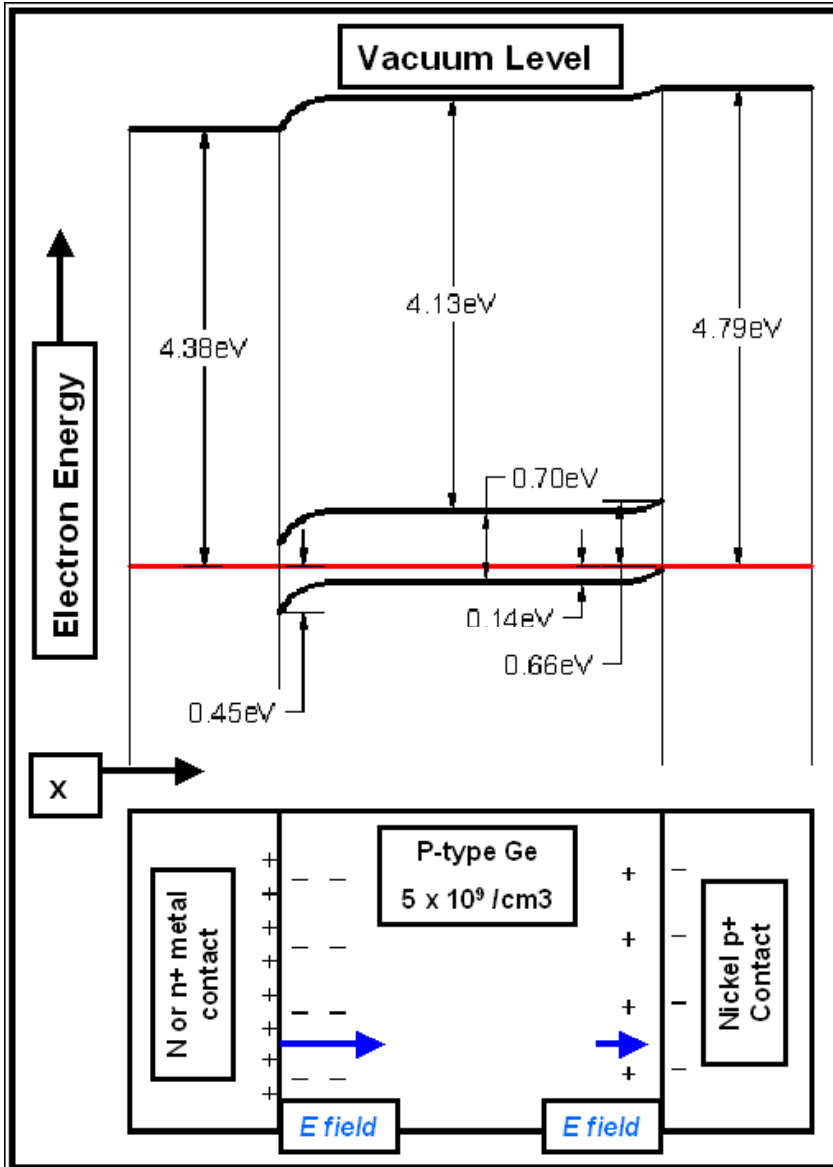
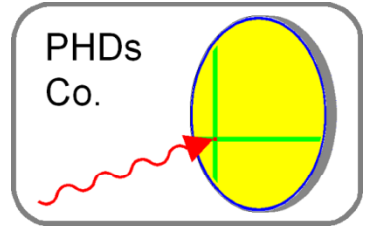
Resistivity is far too low

Contacts must form charge-injection barriers

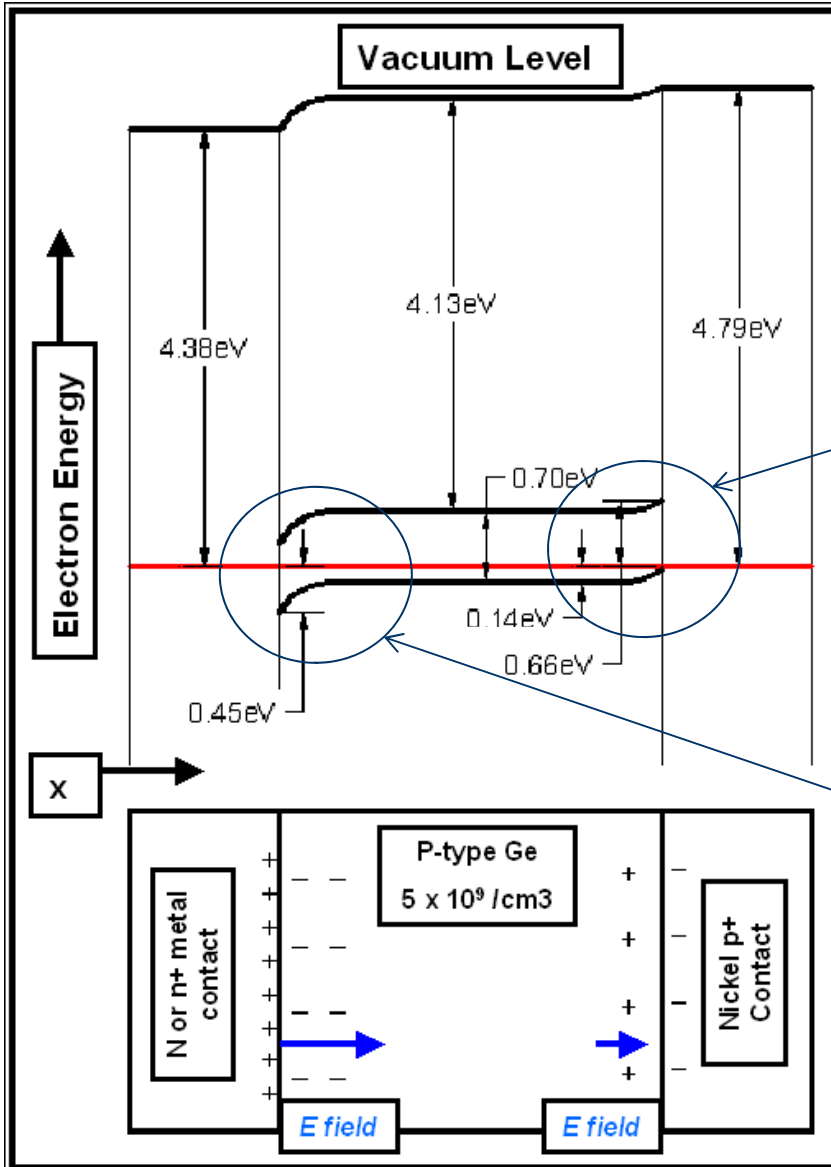
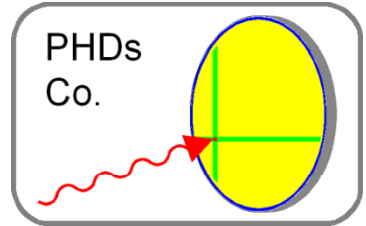
Rectifying and Blocking germanium detector contacts



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Rectifying and Blocking germanium detector contacts

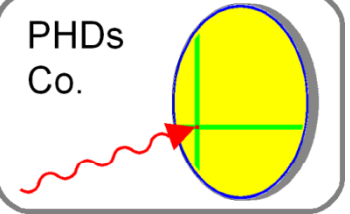


The surface (interface states) of crystalline HPGe is p type. Most materials form an electron barrier – historic dilemma.

Lithium thermal diffusion (100+ μm) forms the only good, high, hole barrier. 99% of detectors are made with lithium hole barrier.

Rectifying and Blocking germanium detector contacts

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Co.

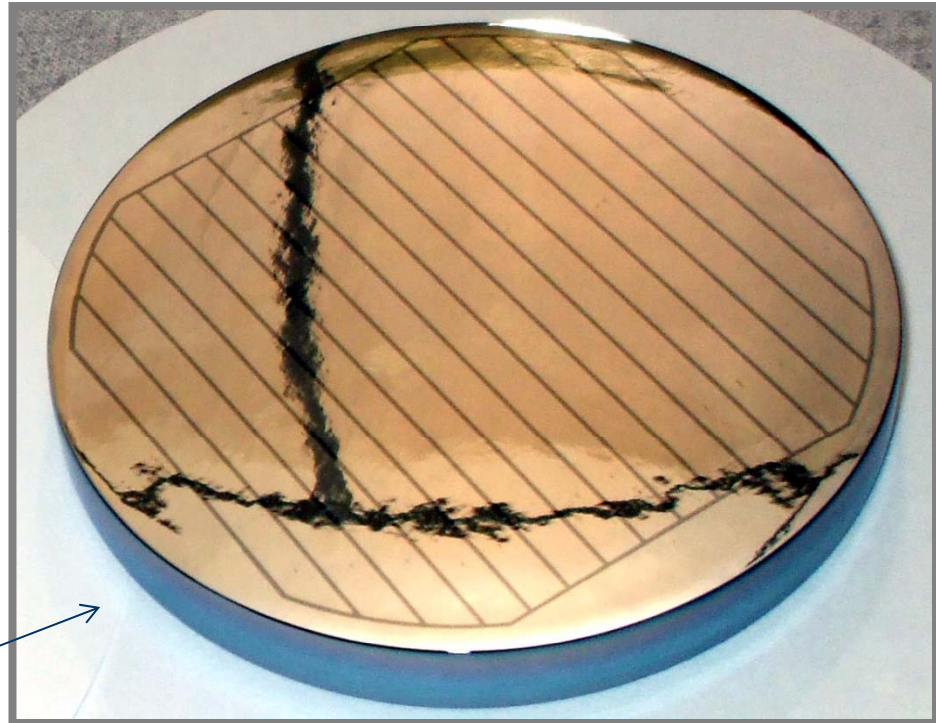


Lithium-diffused contacts are rugged and have great process yield (~ 100%).
However, the thickness limits the use.

x ray detectors require n-type (reverse-electrode) germanium detector.

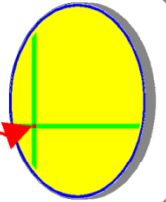
Charged particle spectroscopy is adversely affected by dE/dx in the lithium dead layer.

Position-sensitive applications:
Nuclear physics, nuclear medicine,
.. Lithium contacts are extremely difficult to coarsely segment



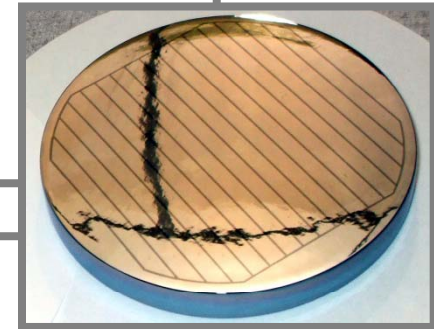
Rectifying and Blocking germanium detector contacts

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Phosphorus implanted n+ contacts (thin) have been used for charged particle detectors – long and dangerous annealing cycles, edge problems, low electric field....

Amorphous germanium contact (thin) can be used, *low barrier height* (0.3-.4 eV) (temperature limited ~ 90 K), yield is questionable over large areas – overall this is the best alternative.

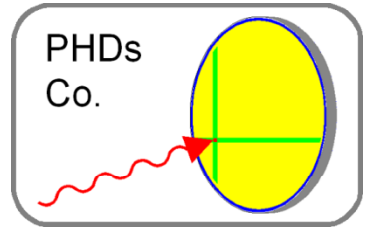


Barrier height is critical

- Lithium hole barrier (n+--p jtn) barrier height ~ 0.7 eV (130 K)
- Amorphous germanium 0.35 eV (avg) (90-95 K)
- $j \sim \exp(-\phi/k_B T)$

A thin (segmented) hole-barrier contact with a high barrier height would be of great benefit to germanium-detector technology.

NPX and NPX-M Germanium Strip Detectors



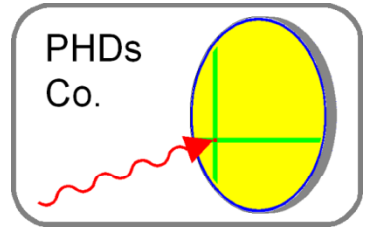
LN₂ Cooled
NPX Systems



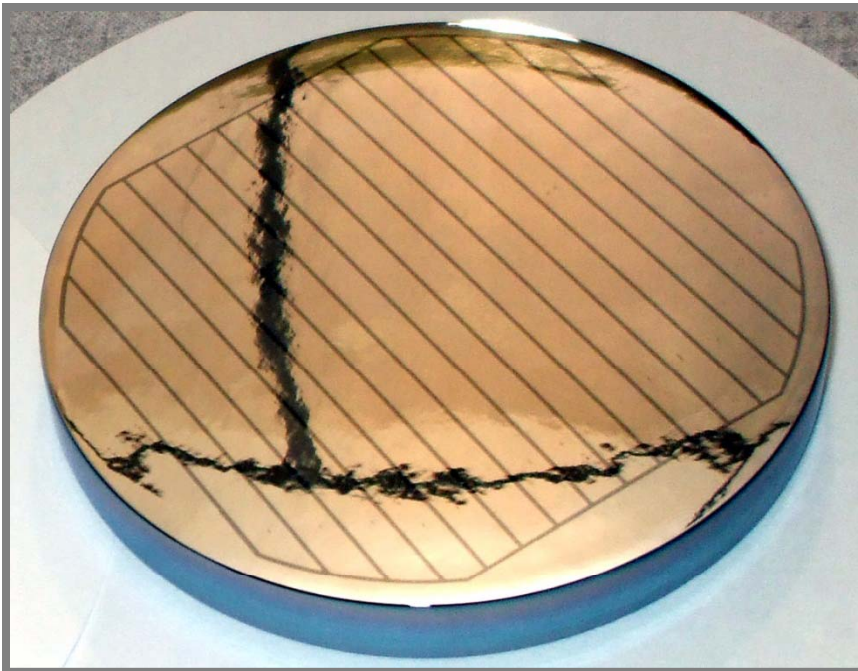
Mechanically Cooled
NPX-M Systems



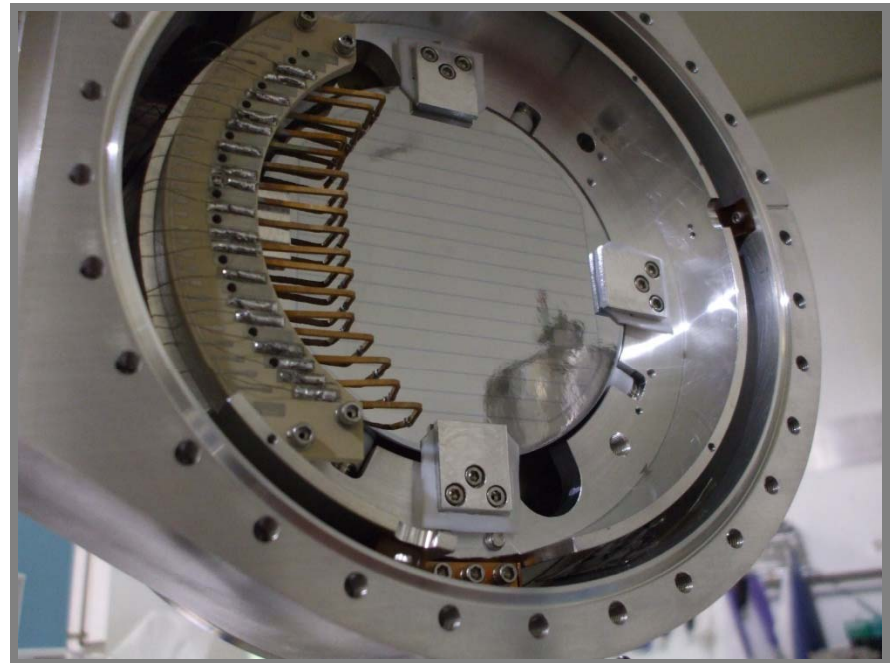
NPX and NPX-M Germanium Strip Detectors



16 x 16 Strip NPX Detector

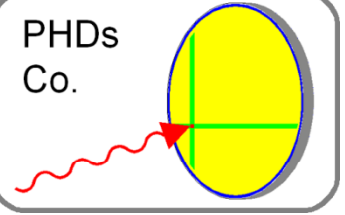


NPX Detector in a cryostat



A better hole barrier contact
could make the gaps narrower

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Phase I: Are there any low work-function metals that form a useful hole barrier?

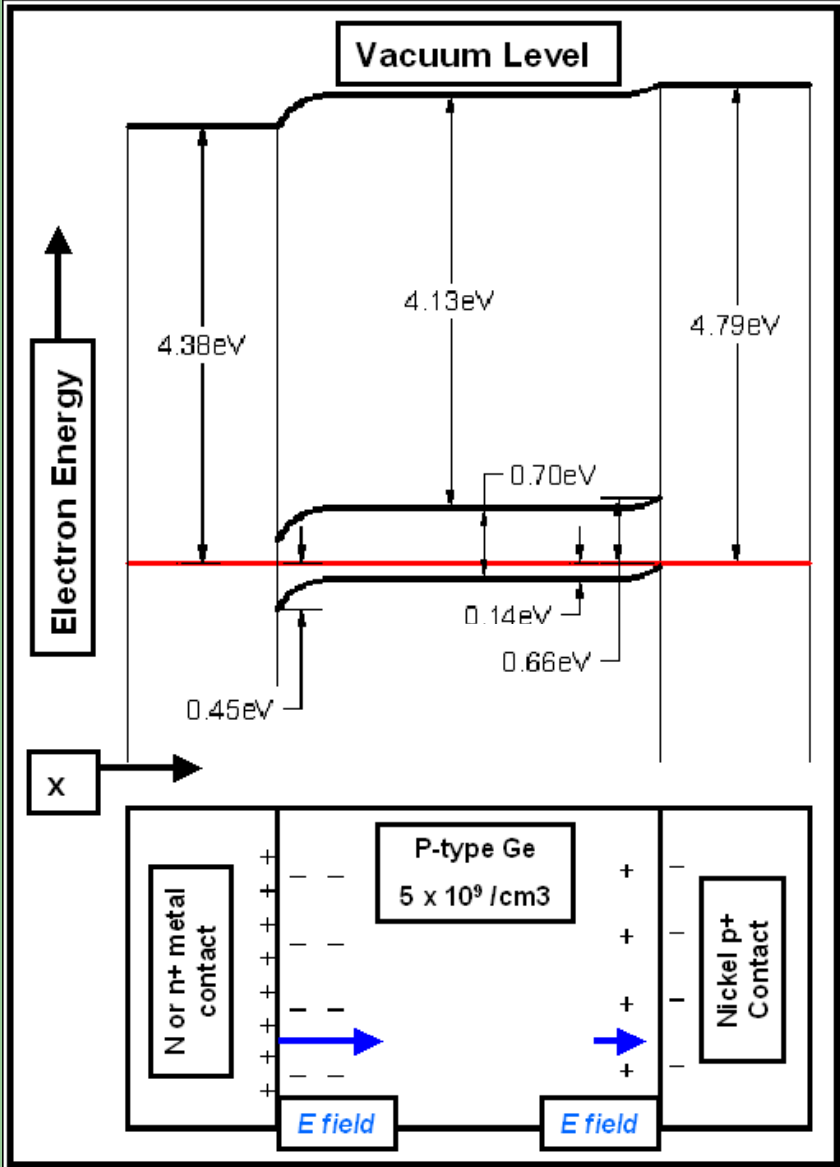
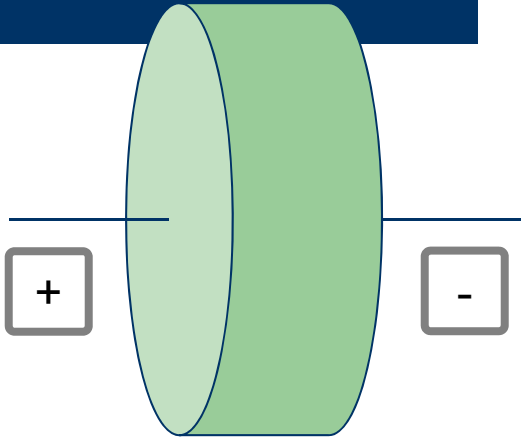
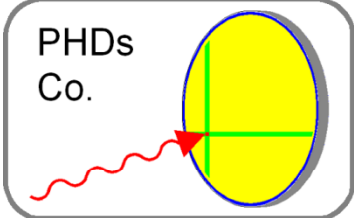
Yes, **Yttrium (A = 39)** metal forms a hole barrier that can function as a detector contact.

Phase II Program Goals:

1. Study and optimize the yttrium contact using test detectors
2. Work out photolithography and processing for full-sized detector fabrication – demonstrate.

Better, less expensive (higher yield), more reliable NPX-M detectors with narrower gaps will be available for nuclear physics.

Metal Selection



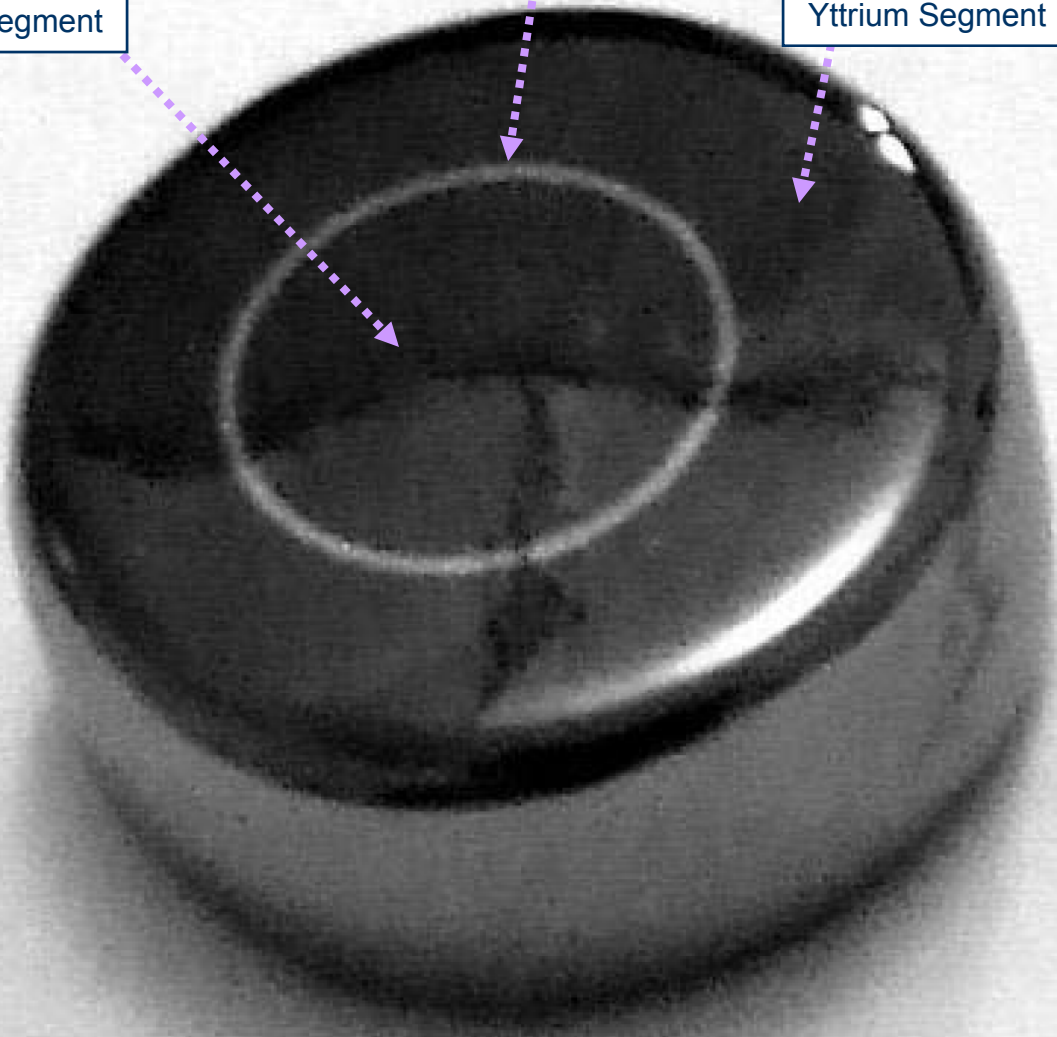
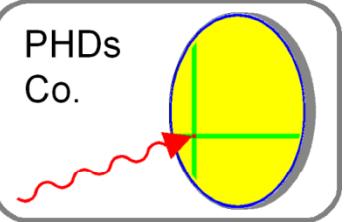
Metal	Work function (eV)	Barrier Type
Nickel	5.2	p+
Chromium	4.5	p+
Gold	5.1	p+
Palladium	5.1	p+
Platinum	5.7	p+
Germanium	~ 5	n-p
Silver	4.3	not n
Samarium	2.7	not n
Antimony	4.5	slightly n
Yttrium	3.1	n+
Niobium	4.3	?

1. Low work function
 2. Can be handled (not horribly toxic)
 3. Produces n-type interface states on Ge
- The most electropositive metals are Li, Na, K, Rb, Cs, (can't be handled easily)

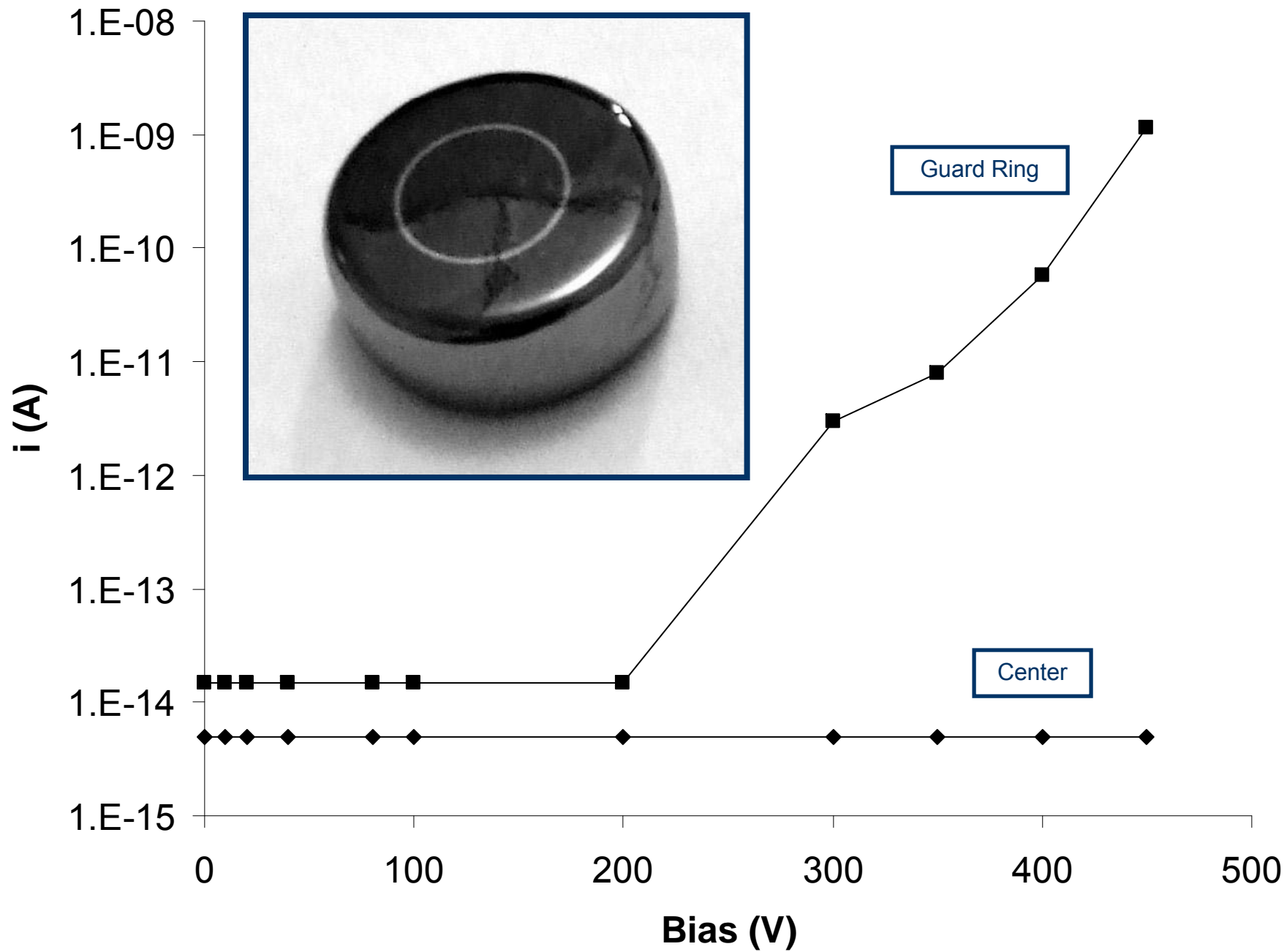
Center
Yttrium
Segment

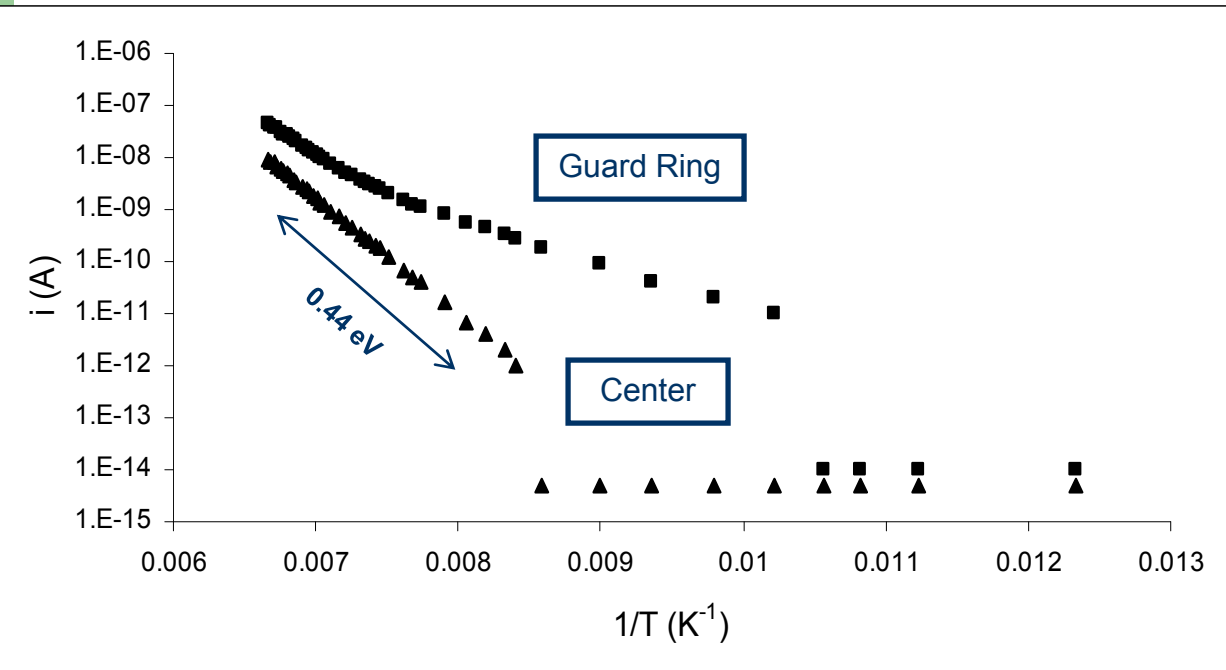
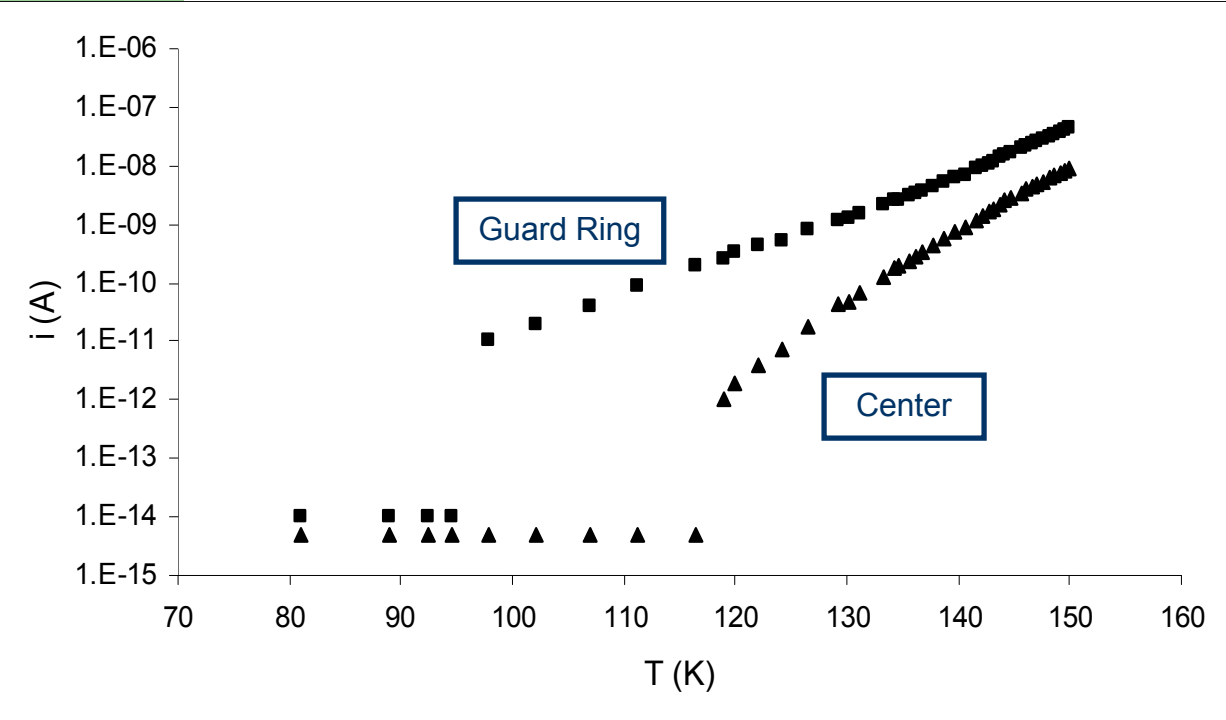
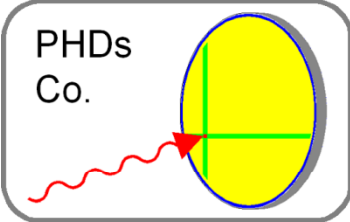
Inter-segment
Gap

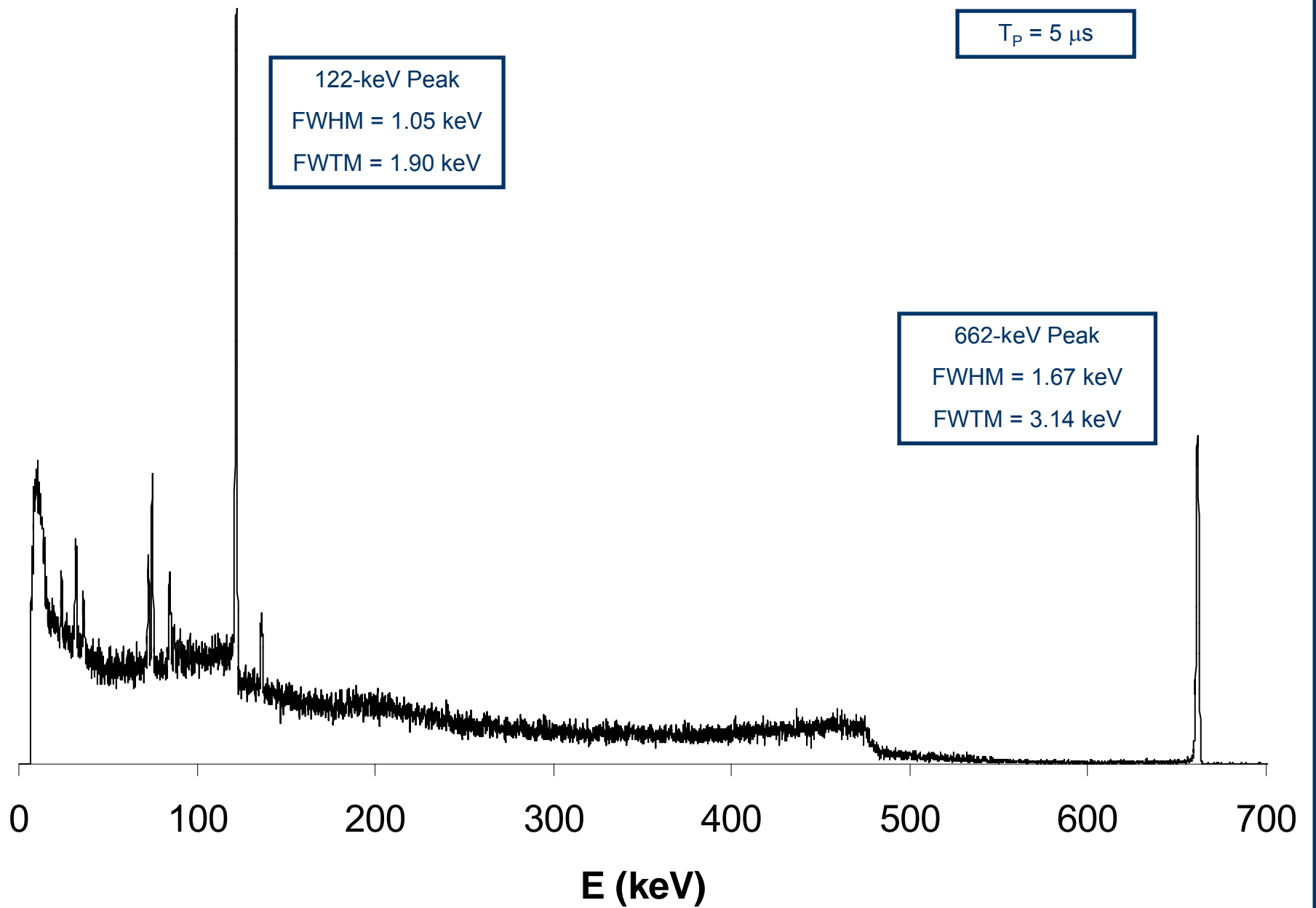
Guard-ring
Yttrium Segment

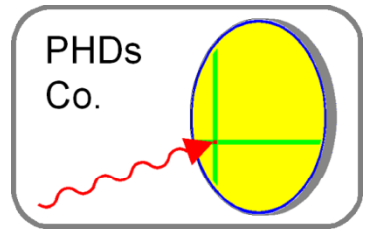


Yttrium test detector (20 mm diameter)









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Yttrium hole-barrier contacts for germanium semiconductor detectors

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ABSTRACT

Sputtered yttrium metal forms a thin hole-barrier contact on both p- and n-type germanium semiconductor detectors. Yttrium contacts can provide a sufficiently high hole barrier to prevent measurable contact leakage current below ~ 120 K. Detectors having yttrium contacts produce good gamma-ray spectroscopy data.

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1. Introduction

Germanium semiconductor single-particle radiation detectors require both electron-barrier and hole-barrier contacts to provide full depletion and sufficient electric field for good charge-carrier collection while blocking the flow of significant leakage current. In addition, the contacts must provide a sufficiently conductive electrical connection to the germanium to avoid series noise problems. Negatively biased electron-barrier contacts can be fabricated using several well developed technologies. Electron-barrier contacts can be fabricated by deposition of thin (~ 1000 Å) metal layers directly onto the crystalline germanium surface. Gold, nickel, chromium, platinum, and palladium have been demonstrated to form good Schottky electron barriers on germanium detectors [1]. Most detector manufacturing now relies on thin boron-implanted p+ contacts to provide the electron-barrier contact. All these electron-barrier contacts are sufficiently thin to allow segmentation into arbitrary contact geometries and provide thin dead-layer entrance windows on the live detector volume for minimal charged-particle energy loss and photon

thick-window contact. Although lithium contacts can be made less thick, they cannot approach the 1000 Å thickness level required for a truly thin entrance window. When a thin outer contact is needed for low-energy photon spectroscopy, the reliance on thick lithium-diffused contacts often forces the use of coaxial and pseudo-coaxial detectors fabricated from n-type germanium. Although extremely rugged and reliable, thick lithium-diffused contacts have greatly limited the use of germanium detectors as transmission detectors in charged-particle telescopes for nuclear physics experiments. Lithium-diffused contacts can be coarsely segmented by grinding through the lithium-diffused layer and/or by the use of relatively wide gap features between segments [2]. A thin hole-barrier contact that can be finely segmented in a convenient manner would be a tremendous improvement in germanium-detector technology.

The search for a thin hole-barrier contact on germanium detectors has continued since 1970s [3,4,5]. Phosphorus-implanted n+ contacts were successfully implemented in long-standing nuclear-physics array and telescope programs. However, fabrication of the phosphorus-implanted n+ contact is an extremely involved

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And Patent Pending

Thank you